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FQP47P06

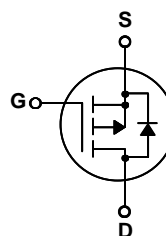
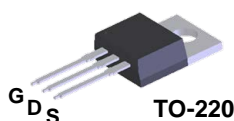
P-Channel QFET® MOSFET - 60 V, - 47 A, 26 mΩ

Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 47 A, - 60 V, $R_{DS(on)} = 26 \text{ m}\Omega @ V_{GS} = - 10 \text{ V}$, $I_D = - 23.5 \text{ A}$
- Low Gate Charge (Typ. 84 nC)
- Low Crss (yp. 320 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating.



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQP47P06	Unit
V _{DSS}	Drain-Source Voltage	-60	V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	-47	A
		-33.2	A
I _{DM}	Drain Current - Pulsed (Note 1)	-188	A
V _{GSS}	Gate-Source Voltage	± 25	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	820	mJ
I _{AR}	Avalanche Current (Note 1)	-47	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	16	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-7.0	V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	160	W
		1.06	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	FQP47P06	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case, Max.	0.94	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink, Typ.	0.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Elerical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-60	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C	--	-0.06	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	μA
		$V_{DS} = -48\text{ V}, T_C = 150^\circ\text{C}$	--	--	-10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-2.0	--	-4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -23.5\text{ A}$	--	0.021	0.026	Ω
g_{FS}	Forward Transconductance	$V_{DS} = -30\text{ V}, I_D = -23.5\text{ A}$ (Note 4)	--	21	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2800	3600	pF
C_{oss}	Output Capacitance		--	1300	1700	pF
C_{rss}	Reverse Transfer Capacitance		--	320	420	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -30\text{ V}, I_D = -23.5\text{ A},$ $R_G = 25\ \Omega$ (Note 4, 5)	--	50	110	ns
t_r	Turn-On Rise Time		--	450	910	ns
$t_{d(off)}$	Turn-Off Delay Time		--	100	210	ns
t_f	Turn-Off Fall Time		--	195	400	ns
Q_g	Total Gate Charge		$V_{DS} = -48\text{ V}, I_D = -47\text{ A},$ $V_{GS} = -10\text{ V}$ (Note 4, 5)	--	84	110
Q_{gs}	Gate-Source Charge		--	18	--	nC
Q_{gd}	Gate-Drain Charge		--	44	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	-47	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-188	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -47\text{ A}$	--	--	-4.0	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -47\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	130	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.55	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 0.43\text{mH}, I_{AS} = -47\text{ A}, V_{DD} = -25\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq -47\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

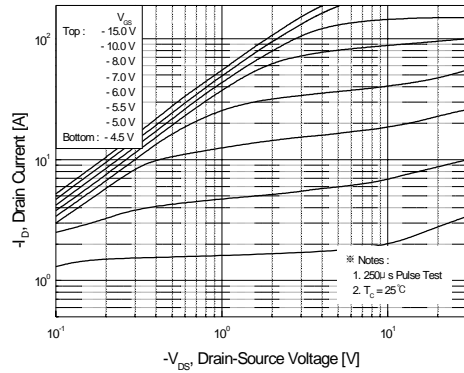


Figure 1. On-Region Characteristics

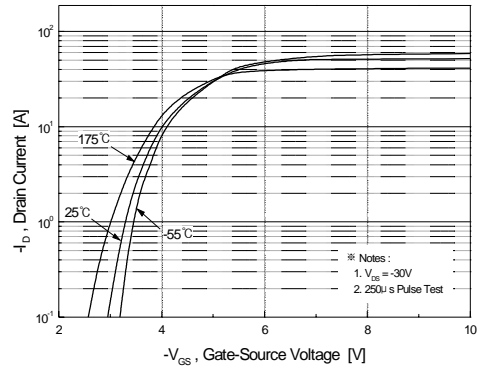


Figure 2. Transfer Characteristics

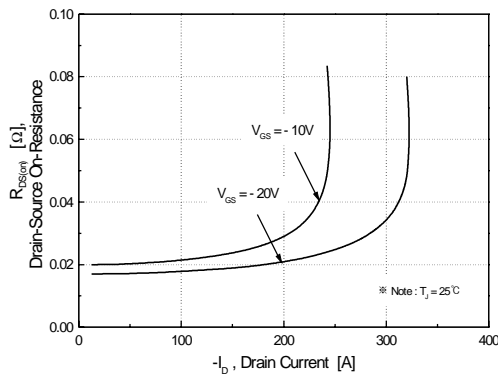


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

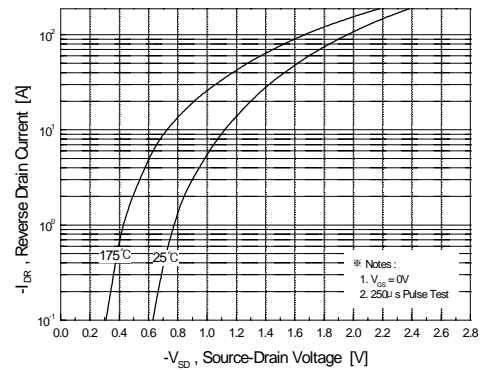


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

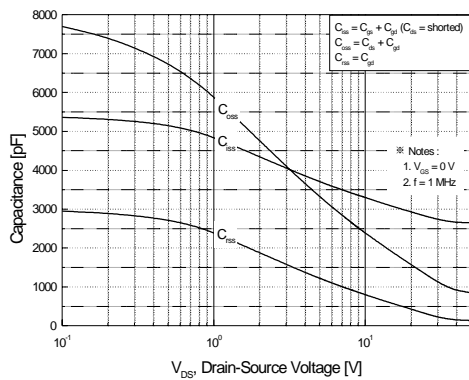


Figure 5. Capacitance Characteristics

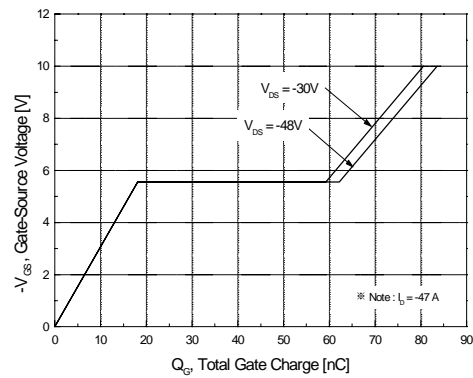


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

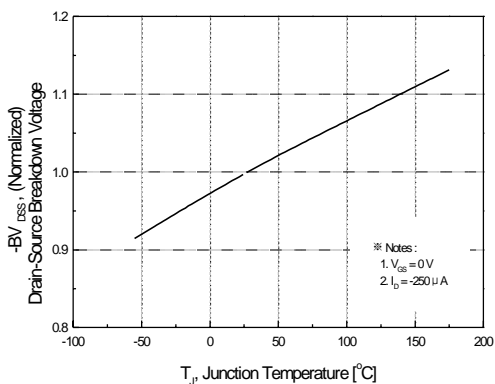


Figure 7. Breakdown Voltage Variation vs. Temperature

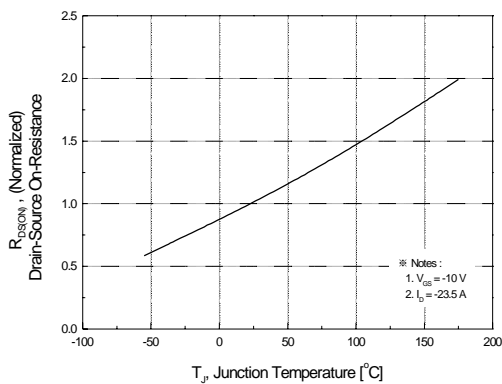


Figure 8. On-Resistance Variation vs. Temperature

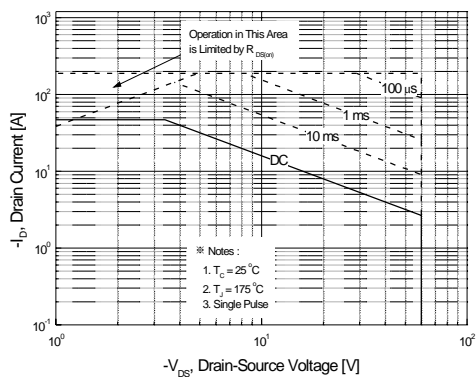


Figure 9. Maximum Safe Operating Area

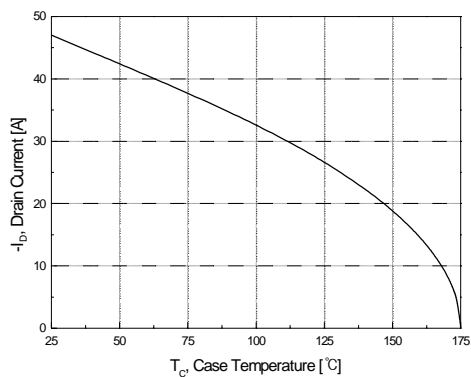


Figure 10. Maximum Drain Current vs. Case Temperature

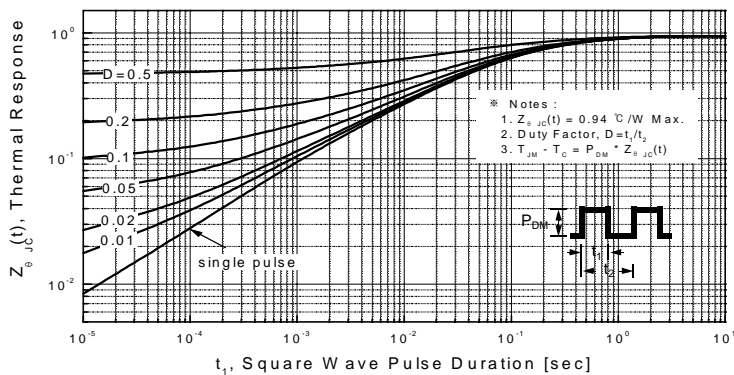
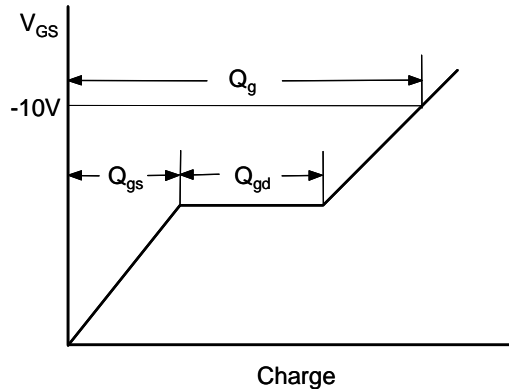
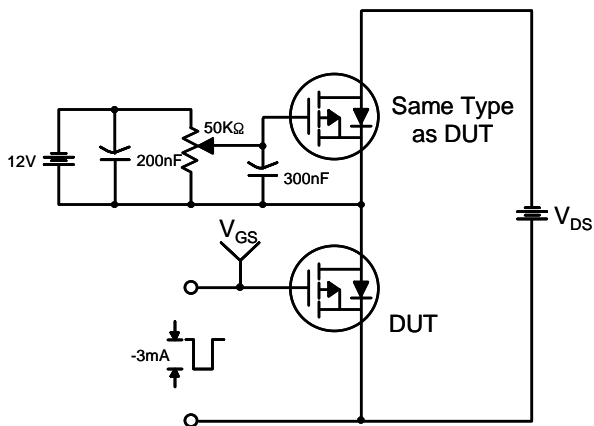
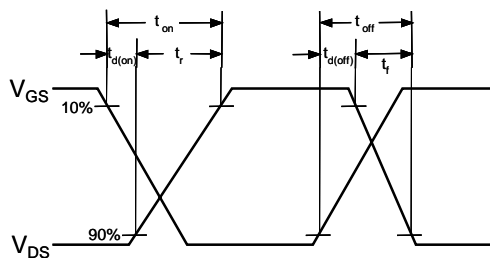
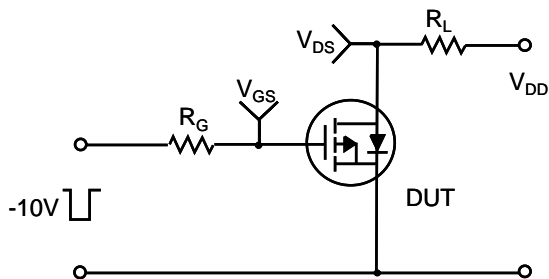


Figure 11. Transient Thermal Response Curve

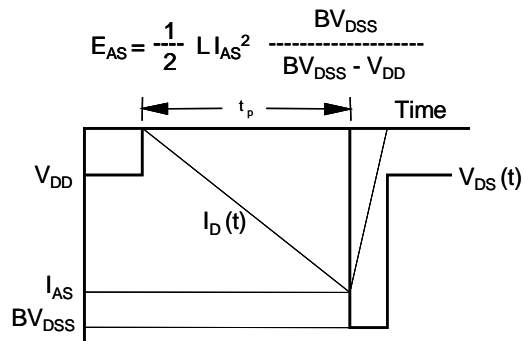
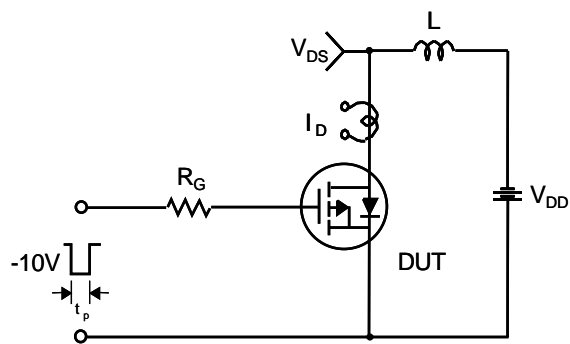
Gate Charge Test Circuit & Waveform



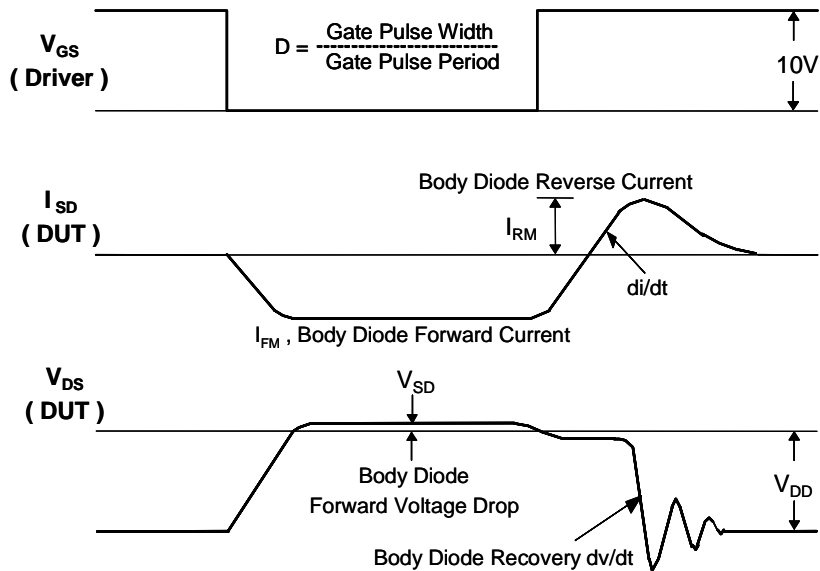
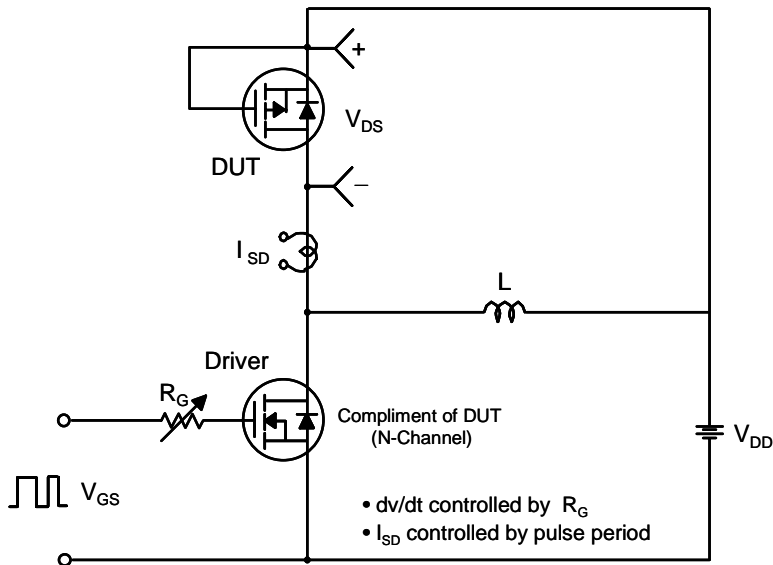
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

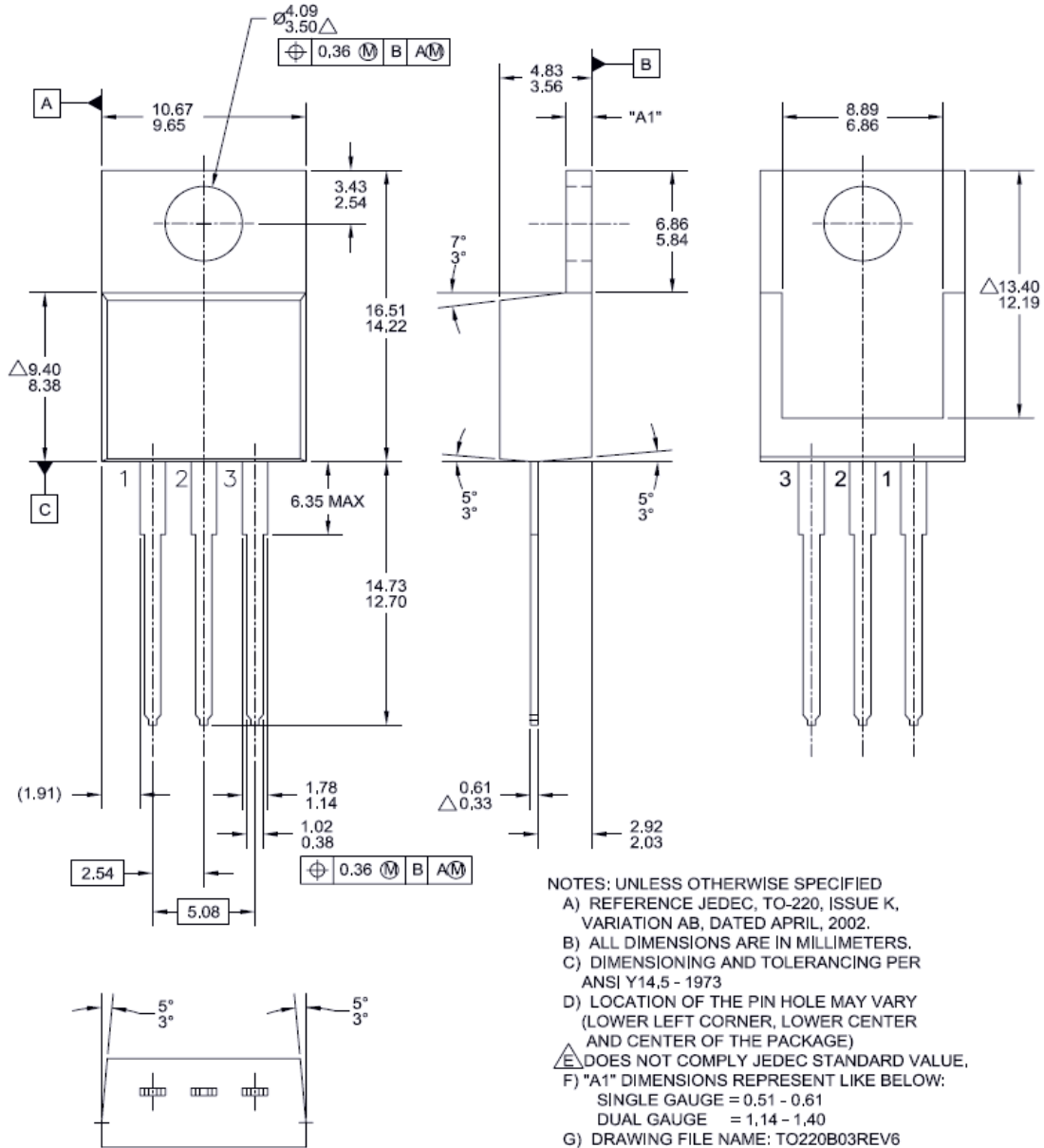


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-220B03



Dimensions in Millimeters

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